

MOSFETs Silicon N-channel MOS (U-MOSX-H)

# TK5R1A08QM

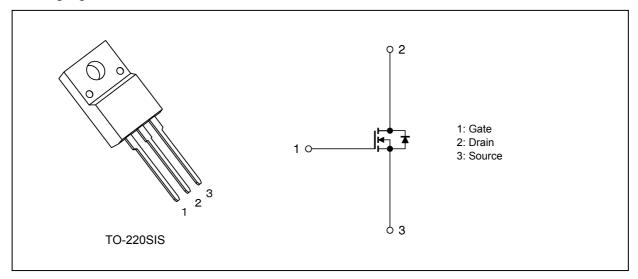
#### 1. Applications

- High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 17 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{oss} = 66 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 4.1 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 80 V)$
- (6) Enhancement mode:  $V_{th} = 2.5 \text{ to } 3.5 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.7 \text{ mA})$

#### 3. Packaging and Internal Circuit



Start of commercial production



## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit		
Drain-source voltage			$V_{DSS}$	80	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>D</sub>	70	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	71	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I <sub>DP</sub>	320	
Power dissipation	(T <sub>c</sub> = 25 °C)		$P_{D}$	45	W
Single-pulse avalanche energy		(Note 3)	E <sub>AS</sub>	36	mJ
Single-pulse avalanche current		(Note 3)	I <sub>AS</sub>	70	Α
Channel temperature			$T_ch$	175	ů
Storage temperature			T <sub>stg</sub>	-55 to 175	
Isolation voltage (RMS)	(t = 1.0 s)		V <sub>ISO(RMS)</sub>	2000	V
Mounting torque			TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics			Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)	R <sub>th(ch-c)</sub>	3.33	°C/W
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	R <sub>th(ch-a)</sub>	62.5	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited 70 A by package capability.

Note 3:  $V_{DD}$  = 64 V,  $T_{ch}$  = 25 °C (initial), L = 5.8  $\mu$ H,  $I_{AS}$  = 70 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	80	_		V
Drain-source breakdown voltage (Note 4)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	60	_	_	
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.7 mA	2.5	_	3.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS} = 6 \text{ V}, I_D = 32 \text{ A}$	_	5.2	7.1	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 35 \text{ A}$		4.1	5.1	

Note 4: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	3980	_	pF
Reverse transfer capacitance	C <sub>rss</sub>			55	_	
Output capacitance	C <sub>oss</sub>		_	1000	_	
Gate resistance	r <sub>g</sub>	_	_	1.6	2.4	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1		47	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	65	_	
Switching time (fall time)	t <sub>f</sub>		_	51	_	
Switching time (turn-off time)	t <sub>off</sub>		_	101	_	

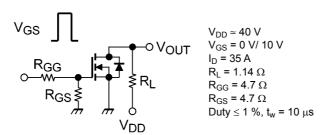


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	$Q_g$	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 35 \text{ A}$	_	54	1	nC
gate-drain)		$V_{DD} \approx 40 \text{ V}, V_{GS} = 6 \text{ V}, I_{D} = 32 \text{ A}$	_	32		
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 35 \text{ A}$	_	14		
Gate-drain charge	$Q_{gd}$		_	12		
Gate switch charge	$Q_{SW}$		_	17	_	
Output charge	$Q_{oss}$	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	66		



## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 5)	I <sub>DRP</sub>	t = 100 μs	_		320	Α
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 35 A, V <sub>GS</sub> = 0 V			-1.2	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 17.5 A, V <sub>GS</sub> = 0 V,	_	45		ns
Reverse recovery charge	$Q_{rr}$	-dI <sub>DR</sub> /dt = 100 A/μs	_	48	_	nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.

#### 7. Marking (Note)

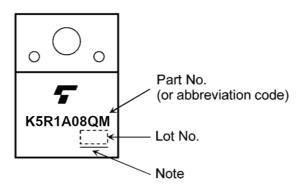


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

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#### 8. Characteristics Curves (Note)

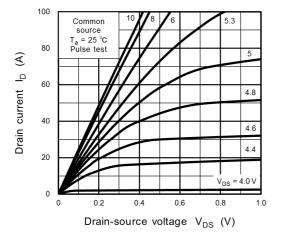
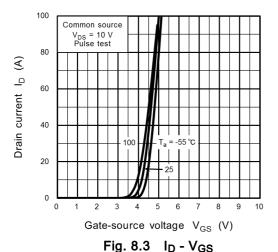


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



Drain-source on-resistance

Common source

T<sub>a</sub> = 25 °C

Pulse test

100

0.1

Drain current  $I_D$  (A) Fig. 8.5  $R_{DS(ON)}$  -  $I_D$ 

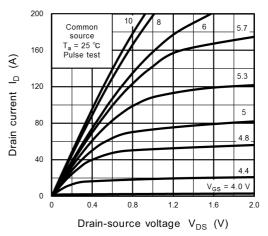


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

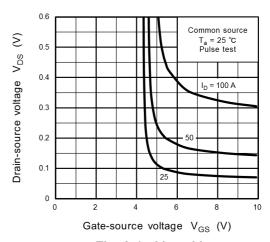


Fig. 8.4 VDS - VGS

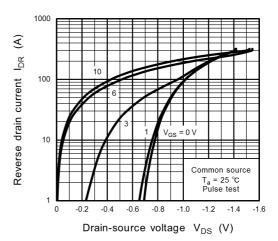


Fig. 8.6 IDR - VDS



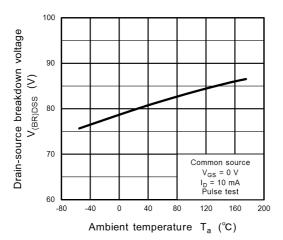


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

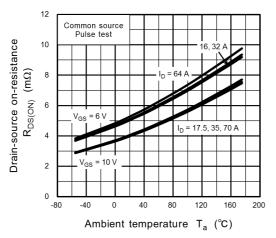


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

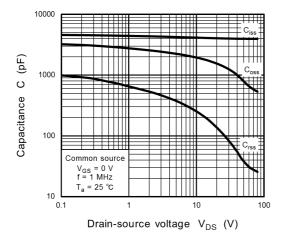


Fig. 8.11 Capacitance - V<sub>DS</sub>

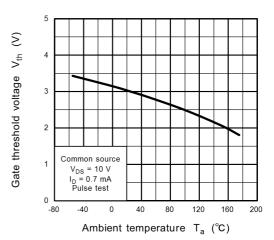


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

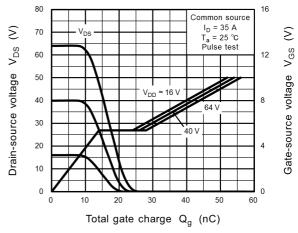


Fig. 8.10 Dynamic Input/Output Characteristics

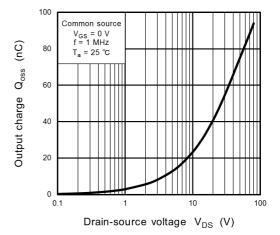


Fig. 8.12  $Q_{oss}$  -  $V_{DS}$ 



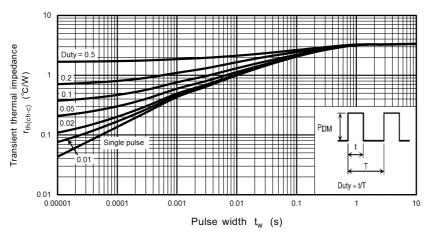
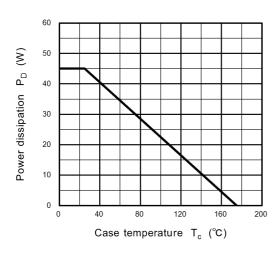


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)



 $\begin{array}{c} \text{1000} \\ \text{D}_{\text{D}} \text{ max (pulse)} * \\ \text{100} \\ \text{ID}_{\text{D}} \text{ max (Continuous)} \\ \text{110} \\ \text{100} \\ \text{D}_{\text{D}} \text{ max (Continuous)} \\ \text{110} \\ \text{110}$ 

Fig. 8.14 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

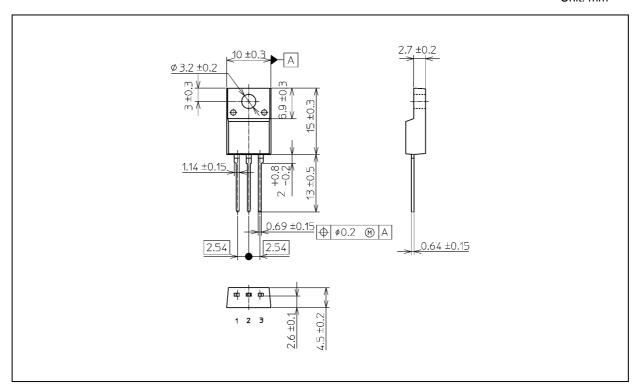
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 1.56 g (typ.)

Package Name(s)	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

Rev.1.0



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